



AMP2011B SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB linear LDMOS design
 Instantaneous wide bandwidth
 Rack mounted system
 Designed for broadband EMI/RFI, Lab, Communication applications
 Suitable for all single channel modulations standards
 Built-in protection circuits
 High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	20 - 100 MHz	
Power Output @ Saturation	1000 Watt Min	CW
Power Output @ P1dB	600 Watt Typ	
Power Gain	60 dB Min	Pin=0dBm for nominal Pout
Power Gain Flatness	3.0 dB p-p Max	
Input Return Loss	-10 dB Max	Relative to 50 Ohm
2-Tone Intermodulation (IMD / IP3)	-30 dBc Min	50dBm/Tone, Δ = 1MHz
Noise Figure	10 dB Max	
Harmonics	-20 dBc Max	
Spurious	-60 dBc Max	Non-harmonic
Operating Voltage	180 - 240 VAC	Single Phase - 50/60Hz
Power Consumption	4000 Watt Max	At rated Pout
Input Power Protection	+3 dBm Max	<10 Sec without damage
Load VSWR Protection	6 : 1 Max	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	430 x 222 x 560 mm	5U - Excluding connectors
Weight	40 Kg. Max	
RF Connectors In/Out	Type-N Female	Front or rear Panel
AC Power / Monitoring Connectors	IEC 60320-C14 / 9 Pin D-Sub	Or equivalent
Safety Interlock Connector	15-Pin Subminiature D-Sub	
Cooling	Built in Fan Cooling	Variable speed
OPTIONAL: Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS-232, USB Optional GPIB/IEEE Interface	

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OUTLINE DRAWING

